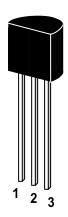
ST 2SD882S-Q/P/E

NPN Silicon Epitaxial Planar Transistor

for the output stage of 0.75W audio, voltage regulator, and relay driver.

The transistor is subdivided into three groups Q, P and E, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25°C)

	Symbol	Value	Unit
Collector to Base Voltage	V _{CBO}	40	V
Collector to Emitter Voltage	V _{CEO}	30	V
Emitter to Base Voltage	V _{EBO}	5	V
Collector Current	I _C	3	А
Power Dissipation	P _{tot}	750	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







ST 2SD882S-Q/P/E

Characteristics at T_{amb}=25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V _{CE} =2V, I _C =1A	Q	h _{FE}	100	-	200	-
	Р	h _{FE}	160	-	320	-
	Е	h _{FE}	250	-	500	-
at V _{CE} =2V, I _C =20mA		h _{FE}	30	-	-	-
Collector Cutoff Current						
at V _{CB} =30V		I _{CBO}	-	-	1	uA
Emitter Cutoff Current						
at V _{EB} =3V		I _{EBO}	-	-	1	uA
Collector to Base Breakdown Vol	tage					
at I _C =100μA		$V_{(BR)CBO}$	40	-	-	V
Collector to Emitter Breakdown V	oltage					
at I _C =1mA		V _(BR)CEO)	30	-	-	V
Emitter to Base Breakdown Volta	ige					
at I _E =10μA		$V_{(BR)EBO}$	5	-	-	V
Collector to Emitter Saturation Vo	ltage					
at I _C =2A,I _B =200mA		$V_{CE(sat)}$	-	-	0.5	V
Base to Emitter Saturation Voltag	е					
at I _C =2A,I _B =200mA		$V_{BE(sat)}$	-	-	2	V
Transition Frequency						
at V _{CE} =5V, I _C =0.1A,f=100MHz		f _T	-	90	-	MHz
Collector Output Capacitance						
at V _{CB} =10V,f=1MHz		Cob	-	45	-	pF









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